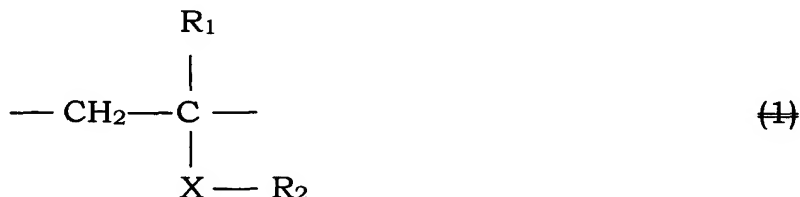


ABSTRACT AMENDMENT

Replace the Abstract with:

A via-filling material ~~comprising includes~~ a polymer containing a ~~repeat~~ repeating unit represented by the following formula (1):



wherein ~~R<sub>1</sub> is a member selected from the group consisting one~~ of hydrogen atom, fluorine atom, chlorine atom, bromine atom, and methyl group; ~~R<sub>2</sub> is a member selected from the group consisting one~~ of hydrogen atom, a C<sub>1-3</sub> alkyl group, and a C<sub>1-4</sub> alkyl group in which the hydrogen atom is ~~substituted~~ replaced by at least one kind of atoms of fluorine, chlorine, and bromine atom; and X is ~~---C(=O)O--- or ---S(=O)<sub>2</sub>O---~~ is used as the via-filling material. This via-filling material does not generate ~~deposition deposits~~ around the an opening part of a via hole during plasma etching and provides a semiconductor integrated circuit with high reliability, even when a trench wider than the via hole is formed by plasma etching around the via hole filled with the via-filling material ~~with plasma~~.